

REQUEST FOR RECONSIDERATION

Applicants thank Examiner Huynh for the indication in the Office Action of November 8, 2004 that Claims 24-29 are allowed. Applicants further thank Examiner Huynh for the helpful discussion of November 23, 2004. During the discussion the Examiner indicated that a process of forming a silicon-oxynitride layer directly adjacent to a conducting layer is not encompassed by the disclosure of the English abstract of JP 64-047055.

Independent Claim 18 is amended herein to require that the nitrogen-containing oxide film is formed directly adjacent to the conductive film and over the semiconductor substrate and the insulating film. Support for the amendment is found in Figure 8 and the paragraph bridging pages 9 and 10 of the specification.

The English Abstract of JP 64-047055 discloses the following:

A superficial insulating film 2 is provided onto the surface of a semiconductor substrate 1 and conductive layers 3 and 3 are selectively formed. A silicon oxide layer 4 is built on the semiconductor substrate 1 including the conductive layers 3 and 3. A silicon oxynitride layer 5 is formed in the film covering the silicon oxide layer 4. A silicon glass layer 6 is formed covering the surface of the silicon oxynitride layer nitride layer 5.

In the English Abstract of JP 64-047055 it is disclosed that a silicon oxide layer is between the conductive layer and the silicon oxynitride layer (e.g., layer 4 interposes layers 3 and 5). In contrast to the invention claimed in Claim 18, the silicon oxynitride layer described in the English Abstract of JP 64-047055 is not directly adjacent to the conductive layer(s) because a silicon oxide layer is underneath the silicon oxynitride layer. The prior art silicon oxynitride layer is not directly adjacent to the conductive layer.

Application No. 10/625,730
Reply to Office Action of November 8, 2004

Applicants submit the amendment to independent Claim 18 places Claim 18 in condition for allowance. Applicants respectfully request the passage of all now-pending claims to allowance.

Respectfully submitted,

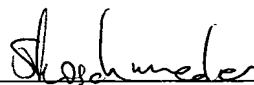
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